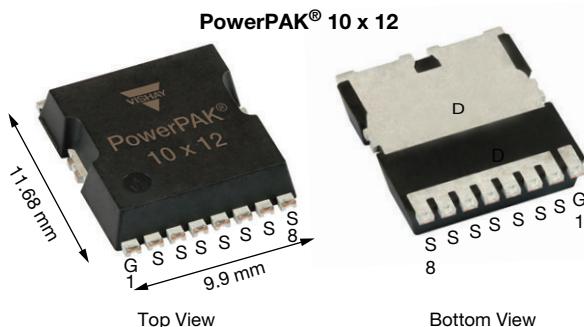


N-Channel 100 V (D-S) MOSFET



FEATURES

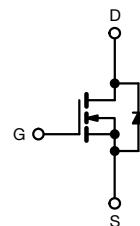
- TrenchFET® Gen V power MOSFET
- Leadership $R_{DS(on)}$ minimizes power loss from conduction
- 100 % R_g and UIS tested
- Standard level FET
- Enhance power dissipation and lower R_{thJC}
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- Automation
- OR-ing and hot swap switch
- Power supplies
- Motor drive control
- Battery management



N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	100
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0014
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5$ V	0.0016
Q_g typ. (nC)	131
I_D (A) ^a	417
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK® 10 x 12
Lead (Pb)-free and halogen-free	SiJK5100E-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ($T_J = 175$ °C)	I_D	417	A
		295	
		74 b, c	
		52 b, c	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	700	
Continuous source-drain diode current	I_S	487	
		15 b, c	
Single pulse avalanche current	I_{AS}	65	mJ
Single pulse avalanche energy	E_{AS}	214	
Maximum power dissipation	P_D	536	W
		268	
		17 b, c	
		8.3 b, c	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	R_{thJA}	6.3	9	°C/W
Maximum junction-to-case (drain)	R_{thJC}	0.21	0.28	

Notes

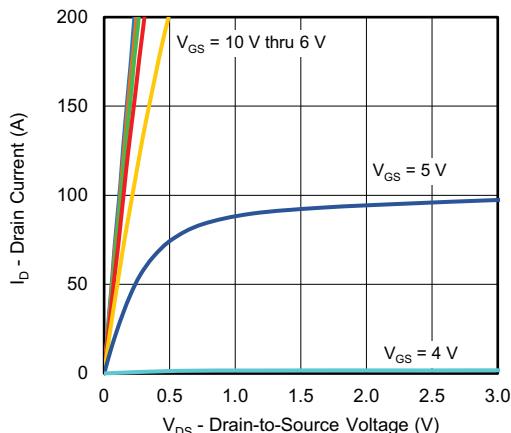
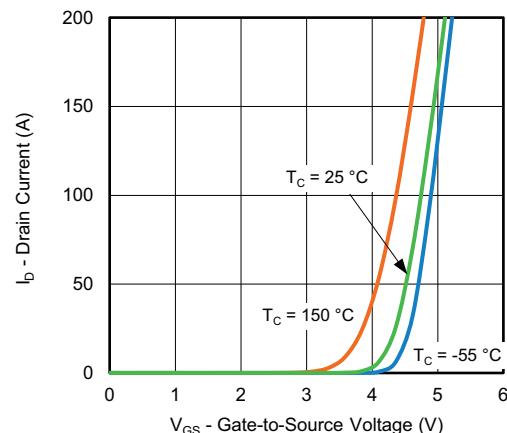
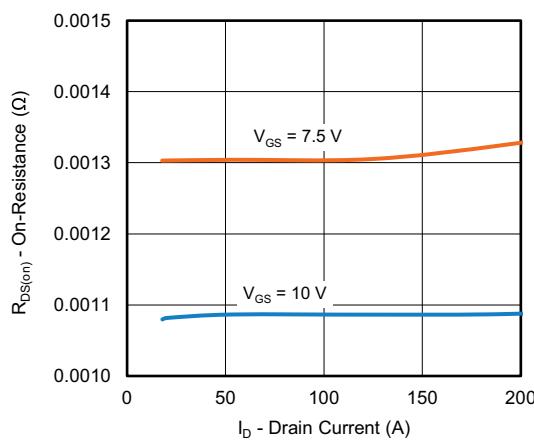
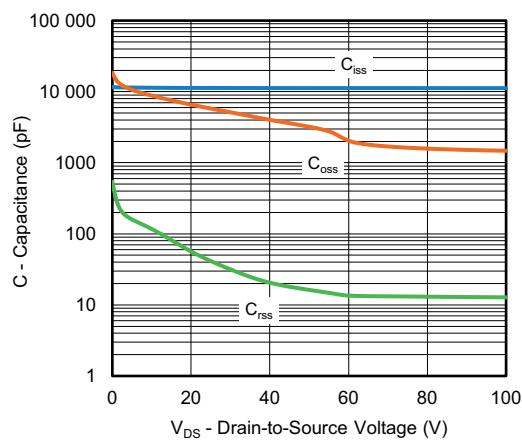
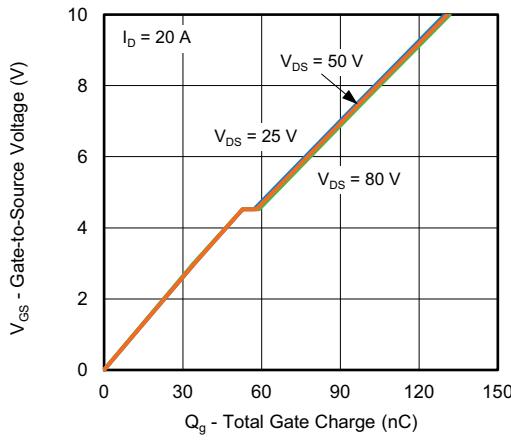
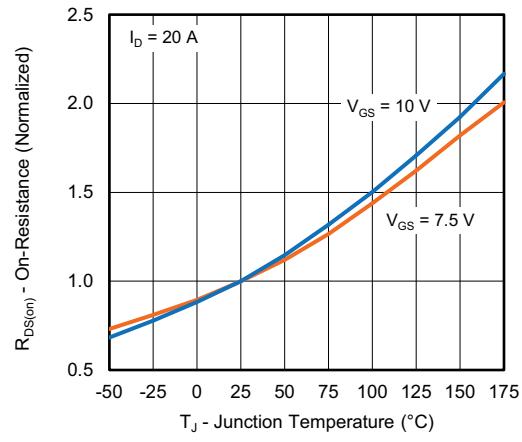
- $T_C = 25$ °C
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?773257). The PowerPAK 10 x 12 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 39 °C/W

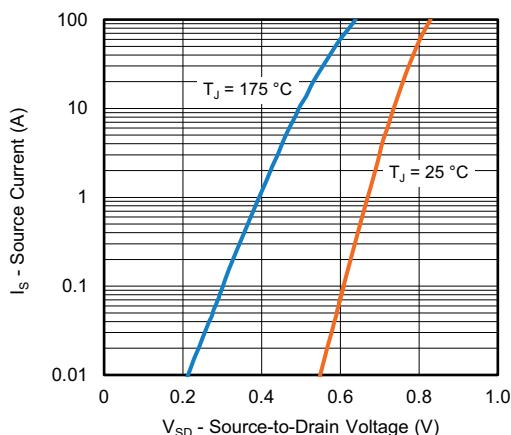
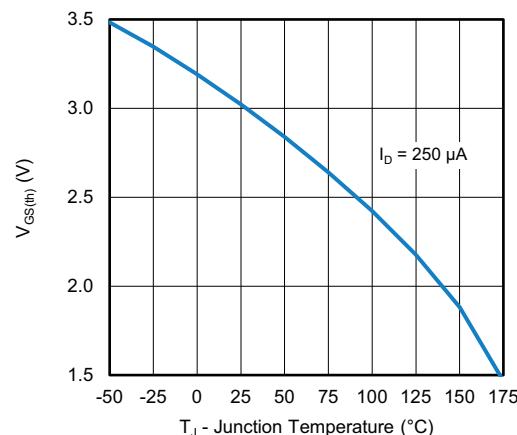
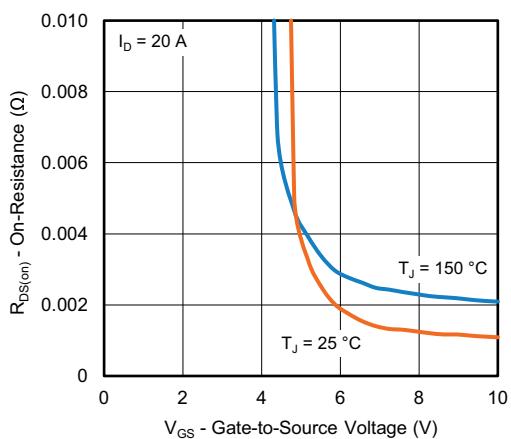
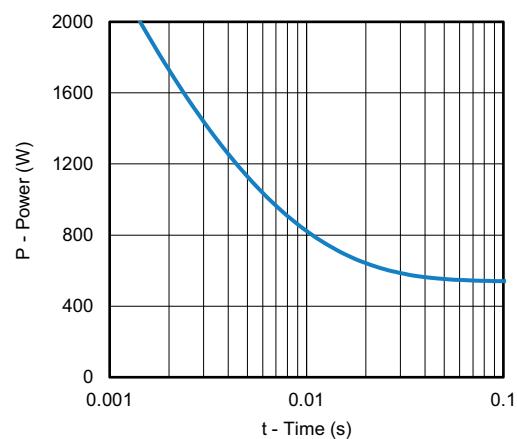
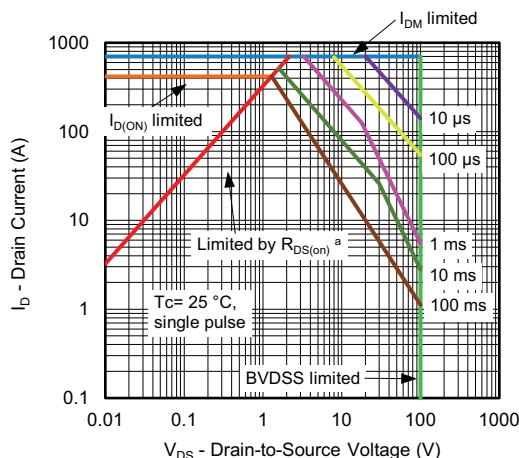
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	100	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10 \text{ mA}$	-	55	-	$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ temperature coefficient	$\Delta V_{GS(\text{th})}/T_J$	$I_D = 250 \mu\text{A}$	-	-8	-	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2	-	4	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 80 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	1	μA
		$V_{DS} = 80 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$	-	-	10	
Drain-source on-state resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 80 \text{ A}$	-	0.00110	0.00140	Ω
		$V_{GS} = 7.5 \text{ V}$, $I_D = 80 \text{ A}$	-	0.00125	0.00160	
Forward transconductance ^a	g_{fs}	$V_{DS} = 25 \text{ V}$, $I_D = 100 \text{ A}$	-	245	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	11 480	-	pF
Output capacitance	C_{oss}		-	3210	-	
Reverse transfer capacitance	C_{rss}		-	17	-	
Total gate charge	Q_g	$V_{DS} = 50 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$	-	131	200	nC
Gate-source charge	Q_{gs}		-	53	-	
Gate-drain charge	Q_{gd}		-	5.3	-	
Total gate charge	Q_g	$V_{DS} = 50 \text{ V}$, $V_{GS} = 7.5 \text{ V}$, $I_D = 20 \text{ A}$	-	97.4	146	
Output charge	Q_{oss}	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	330	-	
Gate resistance	R_g	$f = 1 \text{ MHz}$	0.2	0.8	1.6	Ω
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD} = 50 \text{ V}$, $R_L = 5 \Omega$, $I_D \geq 10 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$	-	32	65	ns
Rise time	t_r		-	15	30	
Turn-off delay time	$t_{d(\text{off})}$		-	54	110	
Fall time	t_f		-	35	70	
Turn-on delay time	$t_{d(\text{on})}$		-	41	80	ns
Rise time	t_r	$V_{DD} = 20 \text{ V}$, $R_L = 5 \Omega$, $I_D \geq 10 \text{ A}$, $V_{GEN} = 7.5 \text{ V}$, $R_g = 1 \Omega$	-	18	35	
Turn-off delay time	$t_{d(\text{off})}$		-	47	95	
Fall time	t_f		-	35	70	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ\text{C}$	-	-	487	A
Pulse diode forward current	I_{SM}		-	-	700	
Body diode voltage	V_{SD}	$I_S = 10 \text{ A}$, $V_{GS} = 0 \text{ V}$	-	0.7	1.1	V
Body diode reverse recovery time	t_{rr}	$I_F = 10 \text{ A}$, $\text{di}/\text{dt} = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$	-	140	280	ns
Body diode reverse recovery charge	Q_{rr}		-	360	720	
Reverse recovery fall time	t_a		-	61	-	ns
Reverse recovery rise time	t_b		-	79	-	

Notes

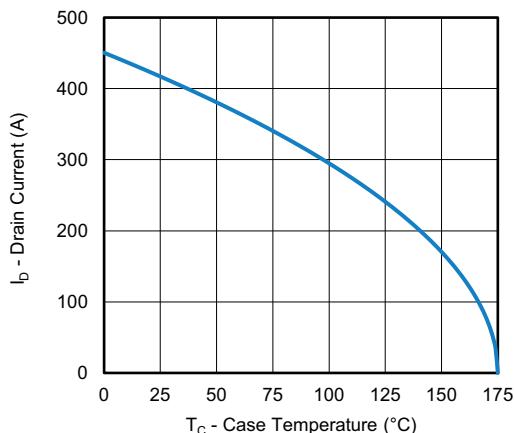
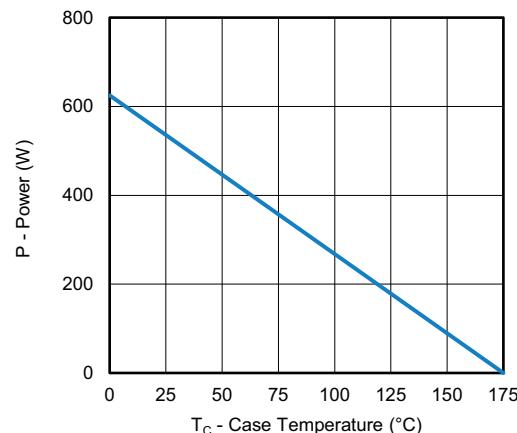
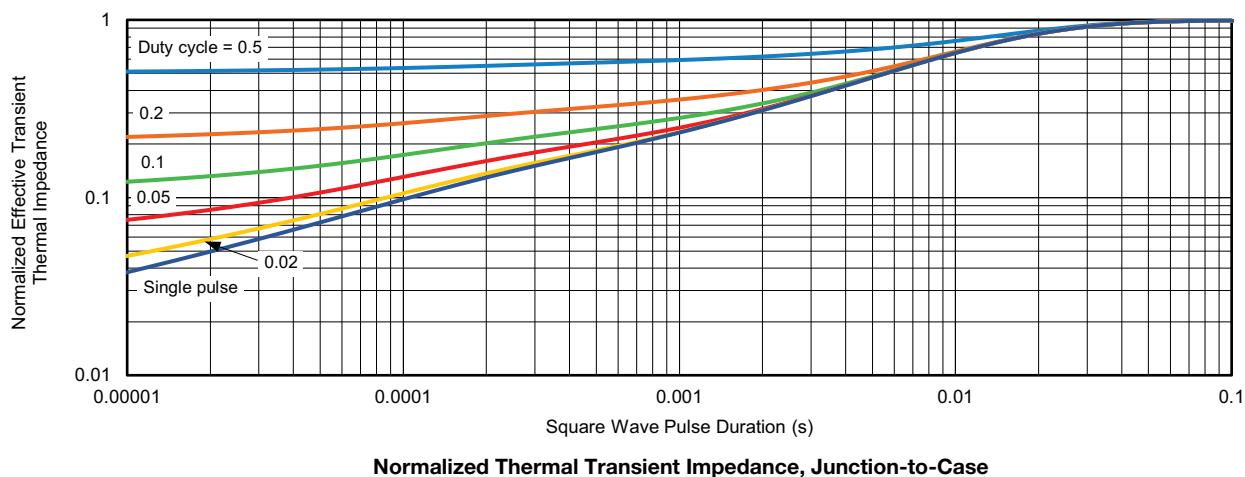
- Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Single Pulse Power, Junction-to-Case

Safe Operating Area, Junction-to-Ambient
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

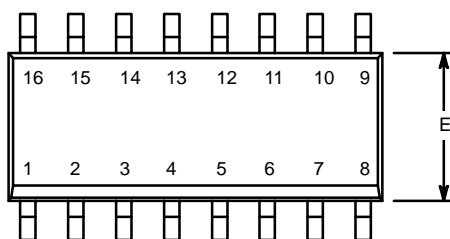
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case

Normalized Thermal Transient Impedance, Junction-to-Case
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

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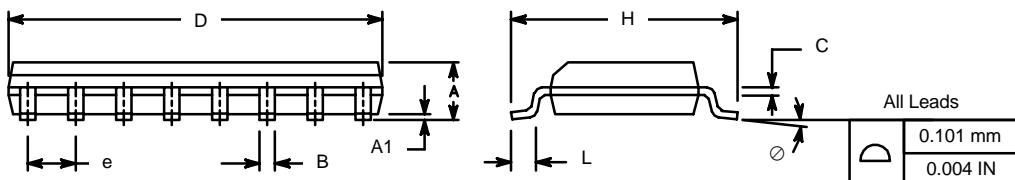
SOIC (NARROW): 16-LEAD

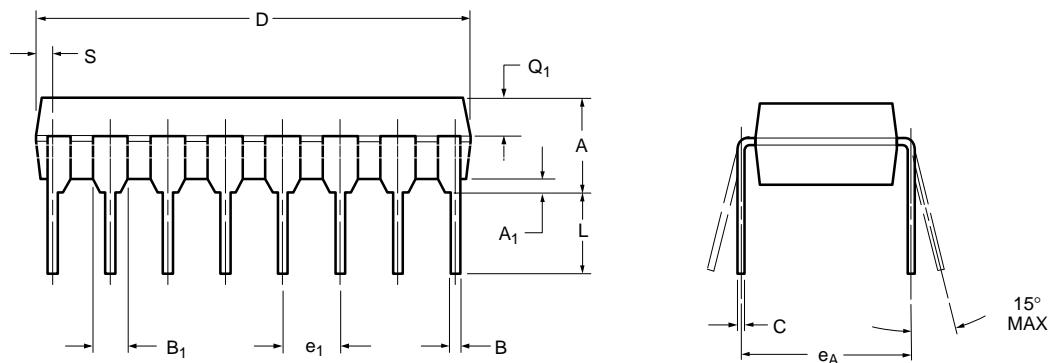
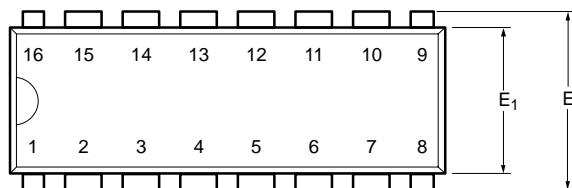
JEDEC Part Number: MS-012



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A₁	0.10	0.20	0.004	0.008
B	0.38	0.51	0.015	0.020
C	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
\emptyset	0°	8°	0°	8°

ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5300

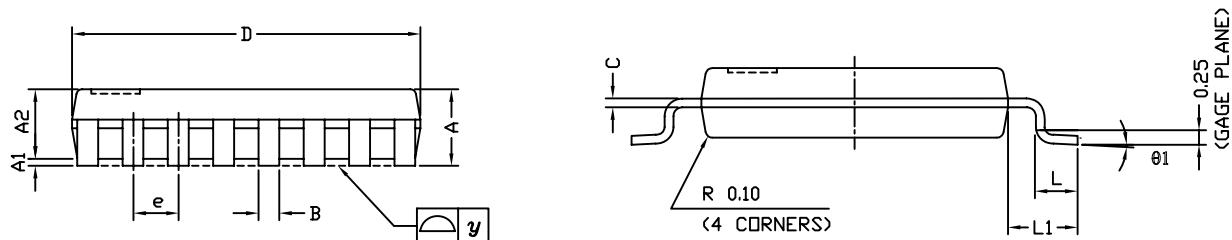
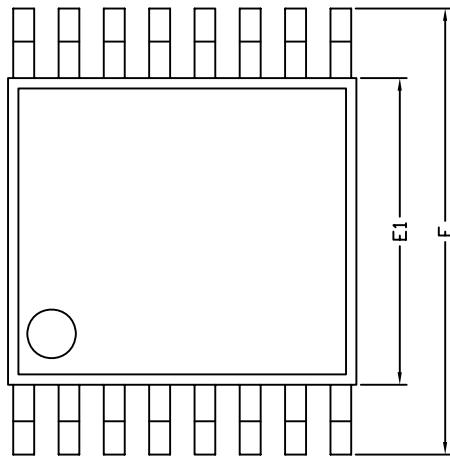


PDIP: 16-LEAD


Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	3.81	5.08	0.150	0.200
A₁	0.38	1.27	0.015	0.050
B	0.38	0.51	0.015	0.020
B₁	0.89	1.65	0.035	0.065
C	0.20	0.30	0.008	0.012
D	18.93	21.33	0.745	0.840
E	7.62	8.26	0.300	0.325
E₁	5.59	7.11	0.220	0.280
e₁	2.29	2.79	0.090	0.110
e_A	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
Q₁	1.27	2.03	0.050	0.080
S	0.38	1.52	.015	0.060

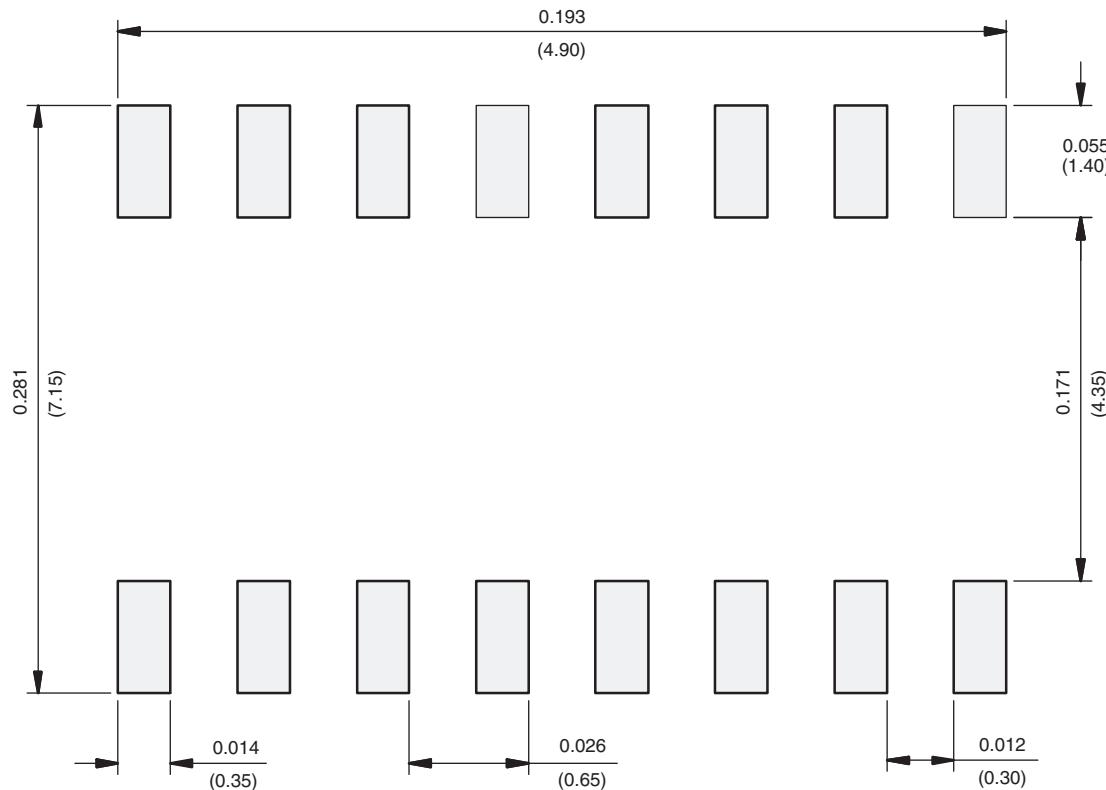
ECN: S-03946—Rev. D, 09-Jul-01
DWG: 5482

TSSOP: 16-LEAD



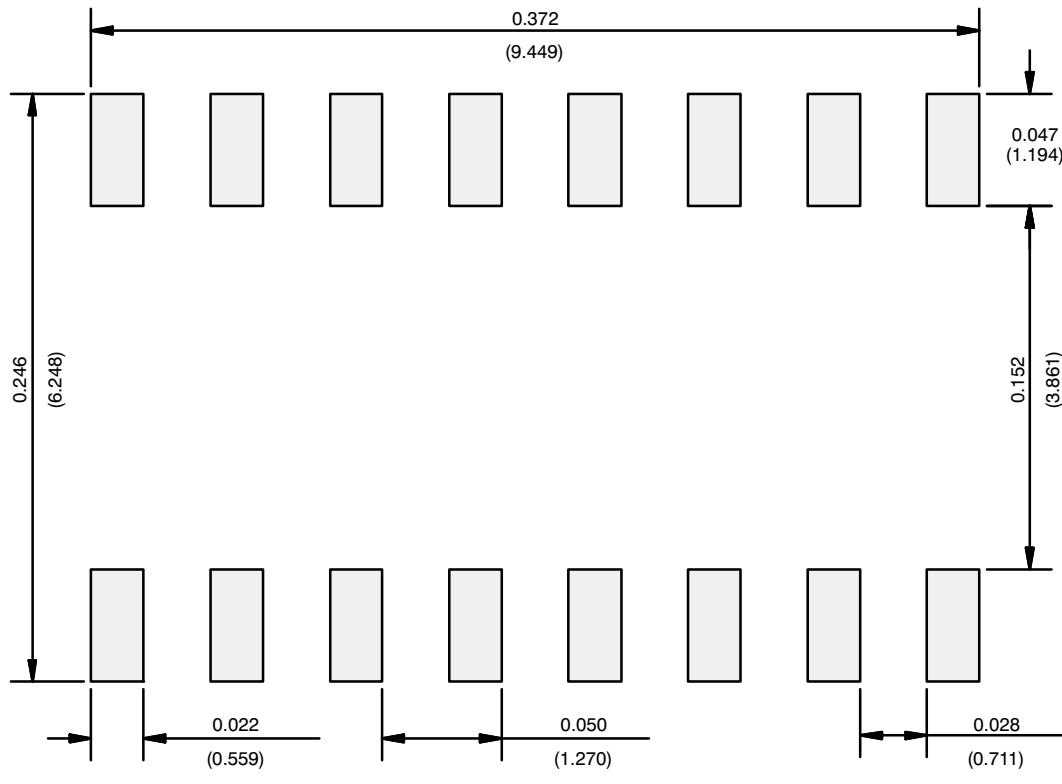
Symbols	DIMENSIONS IN MILLIMETERS		
	Min	Nom	Max
A	-	1.10	1.20
A1	0.05	0.10	0.15
A2	-	1.00	1.05
B	0.22	0.28	0.38
C	-	0.127	-
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
e	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
y	-	-	0.10
theta1	0°	3°	6°

ECN: S-61920-Rev. D, 23-Oct-06
 DWG: 5624

RECOMMENDED MINIMUM PAD FOR TSSOP-16

Recommended Minimum Pads
Dimensions in inches (mm)

RECOMMENDED MINIMUM PADS FOR SO-16



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